

ACCESSORIES

HIGH-POWER CAPABILITIES

Polarization Preserving Beam Sampler (PPBS)

- Dual wedged beam sampler
- UV-FS, ZnSe, CaF₂, BaF₂ options for broad spectral coverage
- High-power handling — beam traps available
- 17.5 mm clear aperture standard, custom options available



PPBS

Power Meters

- Maximum average power up to kW
- Resolution as low as 100 μ W
- Damage resistant absorbers (up to 11 kW/cm² available)
- Absorber spectral range 0.19 - 11 μ m
- Apertures up to 70 mm
- Passive, fan-cooled, and air-cooled options available



Power Meter

CUSTOM SYSTEMS

Large Beam Profiling Systems (LBPS)

- 200 x 200 mm transmissive screen target
- Fully calibrated
- High-power options available



LBPS

Industrial Laser Monitoring System (ILMS)

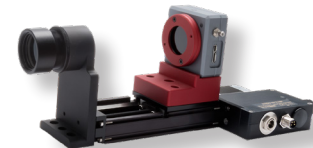
- Incorporates magnification system, high-power attenuator, and camera profiler
- Profile high power beams down to microns in diameter and beyond
- Complex profiles, non-Gaussian profiles, low repetition rate beams



ILMS

TRANSLATION STAGES

- 50, 200, 500, and 1000 mm translation stages
- Fully automated in DataRay software
- ISO11146 compliant M² options — beam propagation analysis, divergence, focus
- Direct measurement of line lasers up to 1000 mm in length with Line Laser Profiling System (LLPS)



M2DU-50-WCD

ULTRAVIOLET and TELECOM/NIR

Ultraviolet

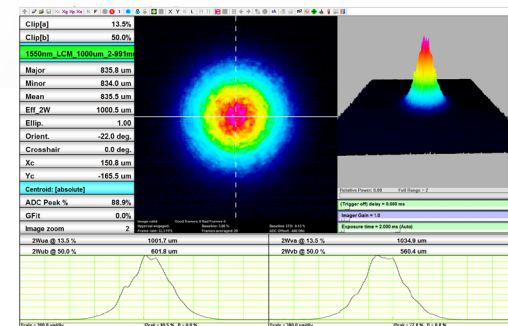
- UV converters
- Reflective UV filter options available



UV Converter

Telecom/NIR

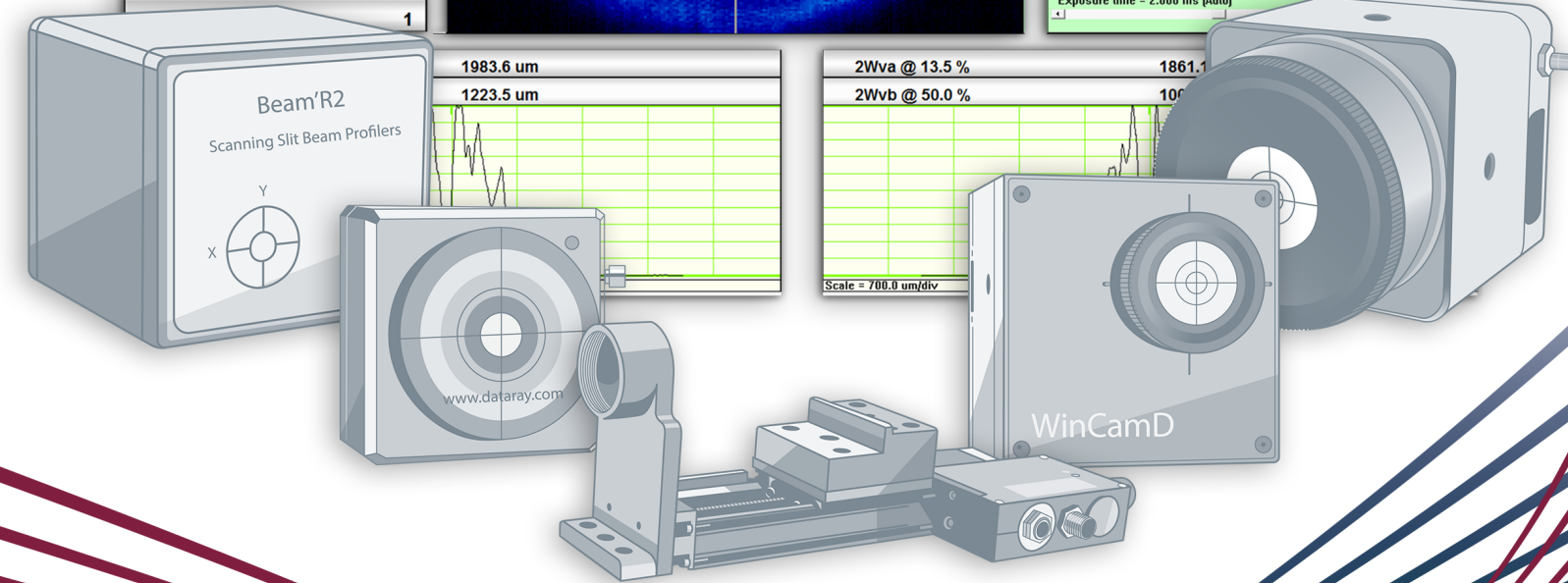
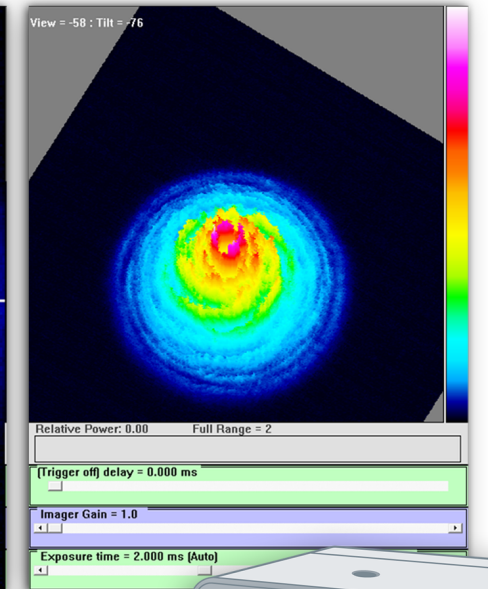
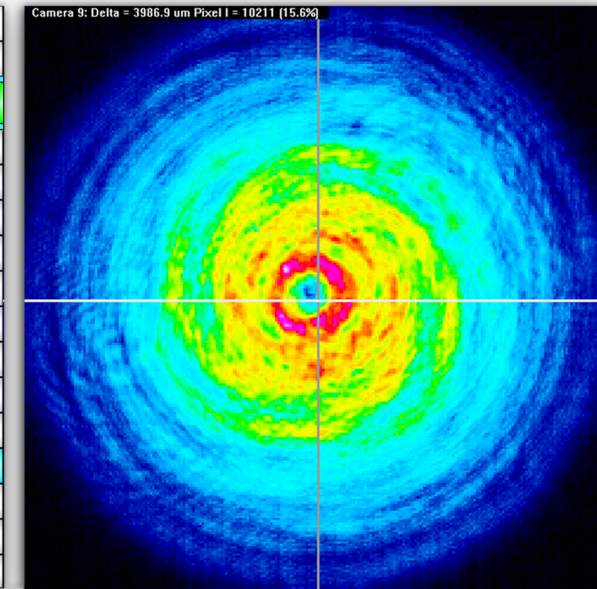
- Phosphor coating 1480 - 1610 nm (converts IR to visible)
 - Economical beam profiling for 1480 - 1610 nm
- Longpass filter option for CMOS profiling up to 1350 nm
- WinCamD-QD-1550 and WinCamD-QD-2000
 - Camera profilers for telecommunications wavelengths and beyond
 - Does not rely on phosphor coating
 - Comparable to InGaAs arrays but large active measurement areas possible (up to 28.8 x 16.2 mm)



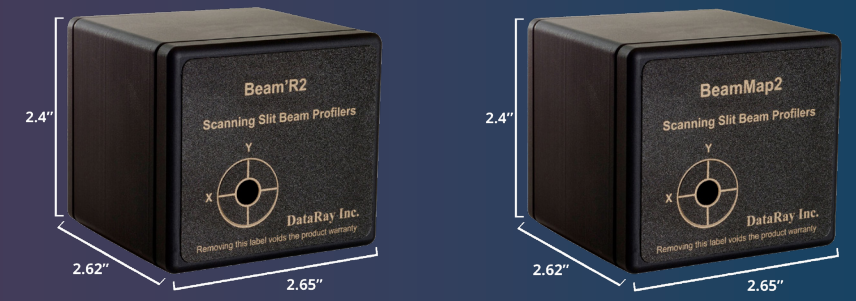
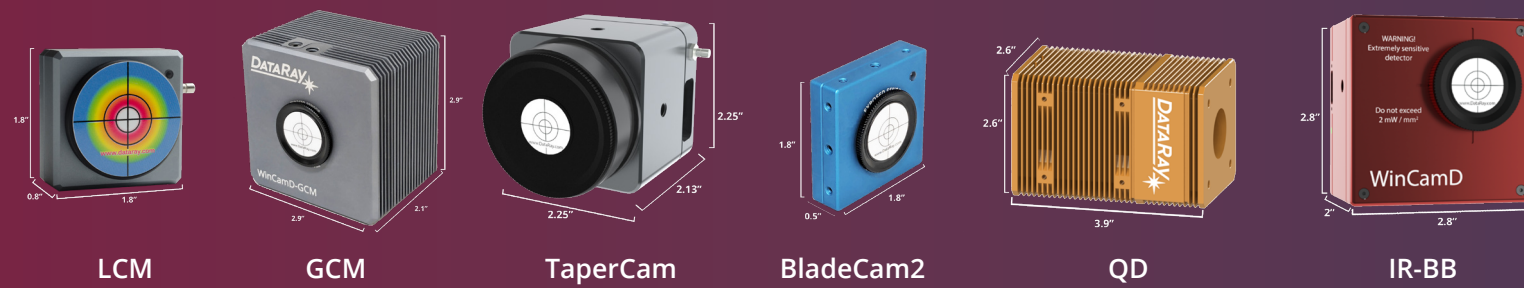
LASER BEAM PROFILER

SELECTION GUIDE

Clip[a]	13.5%
Clip[b]	50.0%
Ready	#1 LCM.10
Major	1758.9 μ m
Minor	1865.9 μ m
Mean	1876.4 μ m
Eff_2W	1632.4 μ m
Ellip.	0.99
Orient.	0.0 deg.
Crosshair	0.0 deg.
Xc	-3039.4 μ m
Yc	-2580.3 μ m
Centroid: [absolute]	
ADC Peak %	95.1%
GFit	78.6%



BEAM PROFILING SYSTEMS



	WinCamD-LCM	WinCamD-GCM	TaperCamD-LCM	BladeCam2-HR/XHR	WinCamD-QD-1550/2000	WinCamD-IR-BB
Product type	Camera	Camera	Camera	Camera	Camera	Camera
Key features	Broad coverage Large sensor	GigE Vision Broad coverage	Extra large active area	Ultra compact Affordable	SWIR beam profiling Extra large sensor options	MWIR/FIR beam profiling High sensitivity
Imaged areas shown actual size.						
Image area (mm)	11.3 x 11.3		25 x 25	6.6 x 5.3 (HR) 6.5 x 4.9 (XHR)	9.6 x 7.7, up to 28.8 x 16.2	10.88 x 8.16
Sensor	1" CMOS			1/2" CMOS	SWIR CQD (1550) eSWIR CQD (2000)	Vanadium oxide (VOx) microbolometer
Resolution	2048 x 2048			1280 x 1024 (HR) 2048 x 1536 (XHR)	From 640 x 512 to 1920 x 1080	640 x 480
Pixel dimensions (µm)	5.5 x 5.5		12.5 x 12.5	5.2 x 5.2 (HR) 3.2 x 3.2 (XHR)	15 x 15	17 x 17
Wavelength range	355 - 1150 nm standard, see back page for others				400 - 1700 nm (1550) 350 - 2000 nm (2000)	Broadband MWIR/FIR: 2 - 16 µm
Interface	USB 3.0 port-powered	GigE Vision	USB 3.0 port-powered	USB 3.0 port-powered	USB 3.0 or GigE	USB 3.0 port-powered
CW or pulsed?	CW, Pulsed, Auto Trigger			CW/Quasi-CW	CW, Pulsed, Auto Trigger	CW, Pulsed >1 kHz
Shutter type	Global			Rolling	Global	Rolling
Single pulse capture PRR	12.6 kHz	25 kHz	12.6 kHz	N/A	<3kHz	N/A
Min. beam diameter (µm)	~55		~125	~52 (HR) ~32 (XHR)	~150	~170
Max. frame rate (Hz)	60+			20+	25	30 (7.5 for export)
Signal to RMS noise	2500:1			1000:1	≥2100:1	≥1000:1
Electronic shutter dynamic range (dB)	44	47	44	41	20	N/A
ADC	12-bit			10-bit	14-bit	14-bit

	Beam'R2	BeamMap2	
Product type	Scanning slit	Scanning slit	
Key features	Integrated X and Y profiles	Real-time XYZθΦ measurement and focus finding Real-time pointing, divergence, and M ² measurements	
Interface	USB 2.0 port-powered		
CW or pulsed	CW/Quasi-CW		
Wavelength range	Si: InGaAs: Extended InGaAs:	190 - 1150 nm 650 - 1800 nm 1800 - 2500 nm	
Best resolution	0.1 µm		
Smallest beam	2 µm (Knife Edge Mode)	5 µm (Si) 10 µm (InGaAs)	
Max. beam diameter (mm)	4 Si	3 InGaAs	2 Extended InGaAs
Update rate	5 Hz real-time (adjustable 2 - 10 Hz)		
M ² measurement	Yes — with M2DU stage		
Locate focus	Yes — real-time		
Pointing/divergence			
Switched gain (Opt. dB)	32 dB		